Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	650	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	1.8
Q_g (Max.) (nC)	48	
Q_{gs} (nC)	12	
Q_{gd} (nC)	19	
Configuration	Single	

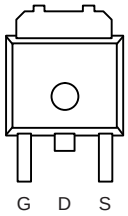
FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Compliant to RoHS directive 2002/95/EC

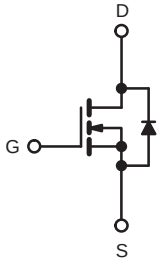
Pb Available

RoHS* COMPLIANT

TO-252



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	650	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current[e]	V_{GS} at 10 V	T_C = 25 °C	I_D	4.5	A
Continuous Drain Current		T_C = 100 °C		4.2	
Pulsed Drain Current[a]			I_{DM}	18	
Linear Derating Factor				0.48	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	325	mJ
Repetitive Avalanche Current[a]			I_{AR}	4	A
Repetitive Avalanche Energy[a]			E_{AR}	6	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	60	W
Peak Diode Recovery dV/dt[c]			dV/dt	2.8	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)[d]	for 10 s			300	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Starting T_J = 25 °C, L = 24 mH, R_G = 25 Ω, I_{AS} = 3.2 A (see fig. 12).
c. I_{SD} ≤ 3.2 A, dI/dt ≤ 90 A/µs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
d. 1.6 mm from case.
e. Drain current limited by maximum junction temperature.

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	2.1	

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		650	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA[d]		-	670	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.5	-	5.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 30 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650 V, V_{GS} = 0 V		-	-	25	µA
		V_{DS} = 520 V, V_{GS} = 0 V, T_J = 125 °C		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 3.1 A[b]	-	-	2.1	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 3.1 A		3.9	-	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	1417	-	pF
Output Capacitance	C_{oss}			-	177	-	
Reverse Transfer Capacitance	C_{rss}			-	7.0	-	
Output Capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 1.0 V, f = 1.0 MHz	-	1912	-	
			V_{DS} = 520 V, f = 1.0 MHz	-	48	-	
Effective Output Capacitance	C_{oss} eff.		V_{DS} = 0 V to 520 V[c]	-	84	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 3.2 A, V_{DS} = 400 V see fig. 6 and 13[b]	-	-	48	nC
Gate-Source Charge	Q_{gs}			-	-	12	
Gate-Drain Charge	Q_{gd}			-	-	19	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 325 V, I_D = 3.2 A, R_G = 9.1 Ω, R_D = 62 Ω, see fig. 10[b]		-	14	-	ns
Rise Time	t_r			-	20	-	
Turn-Off Delay Time	$t_{d(off)}$			-	34	-	
Fall Time	t_f			-	18	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	4	A
Pulsed Diode Forward Current[a]	I_{SM}			-	-	21	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 3.2 A, V_{GS} = 0 V[b]		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 3.2 A, dI/dt = 100 A/µs[b]		-	493	739	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	2.1	3.2	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.
c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}.
d. t = 60 s, f = 60 Hz.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

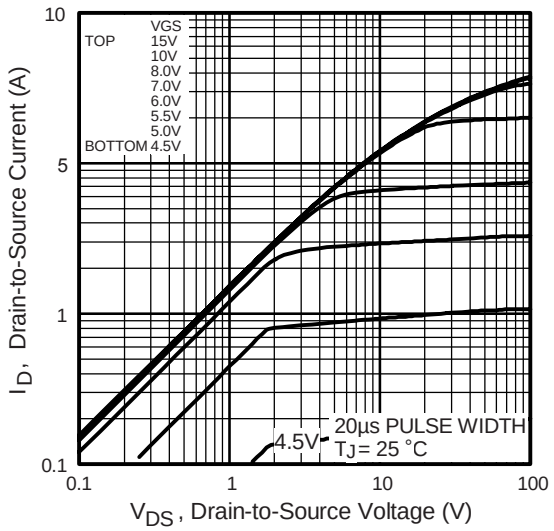


Fig. 1 - Typical Output Characteristics

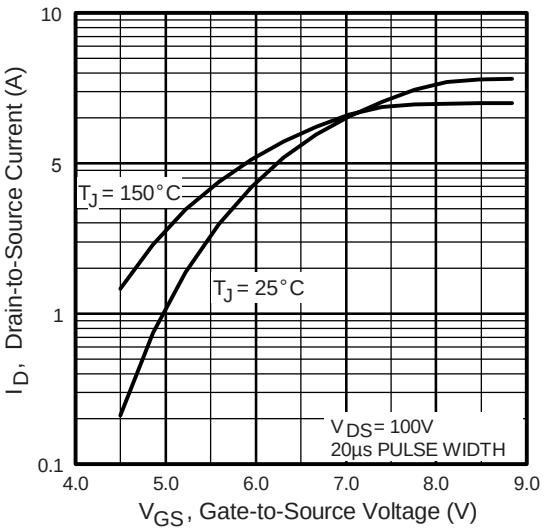


Fig. 3 - Typical Transfer Characteristics

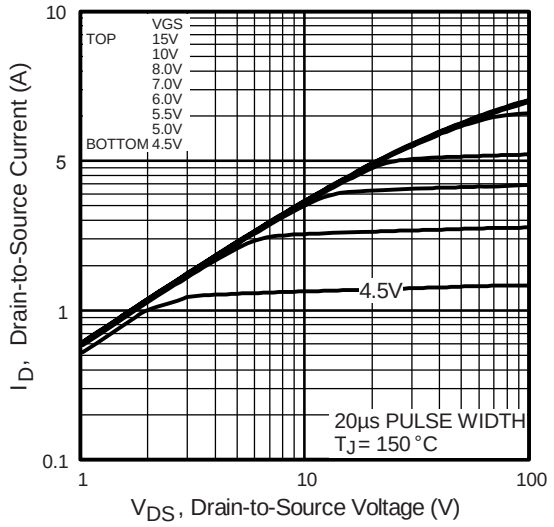


Fig. 2 - Typical Output Characteristics

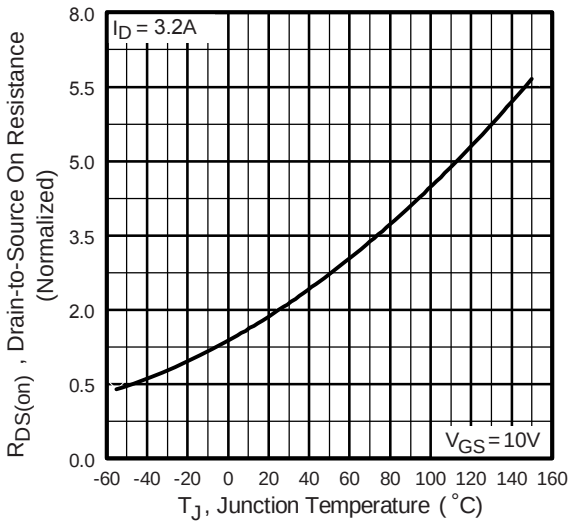


Fig. 4 - Normalized On-Resistance vs. Temperature

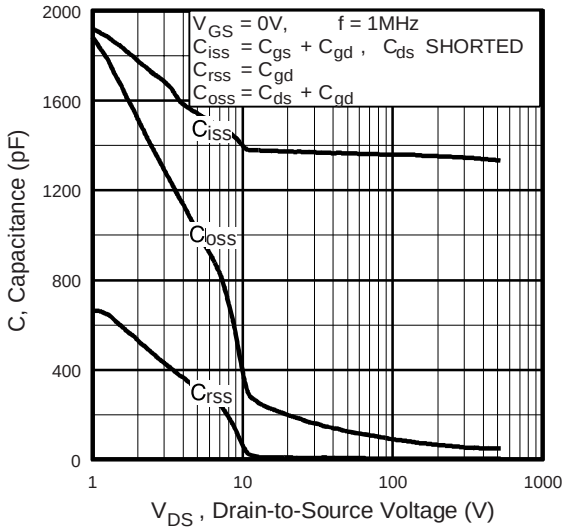


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

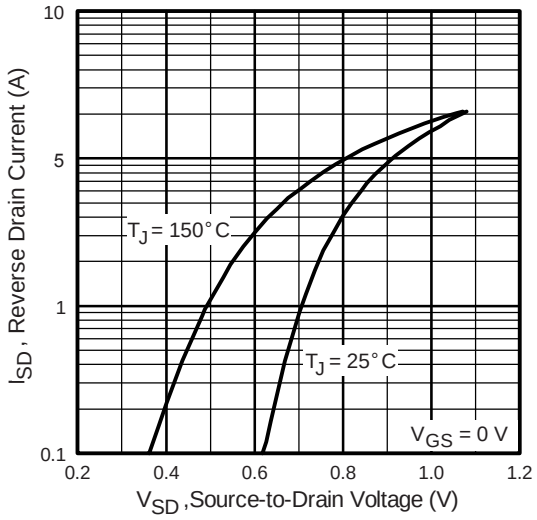


Fig. 7 - Typical Source-Drain Diode Forward Voltage

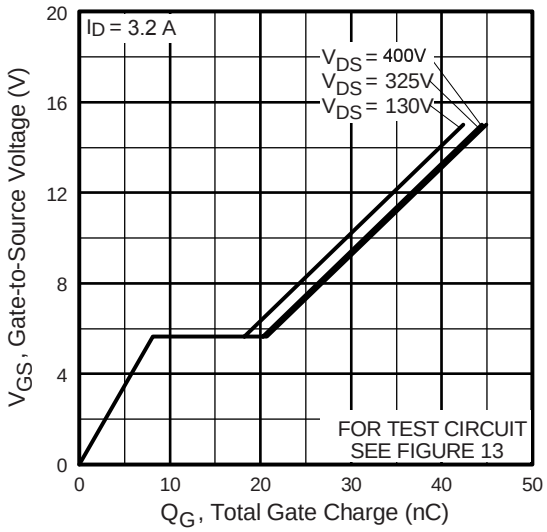


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

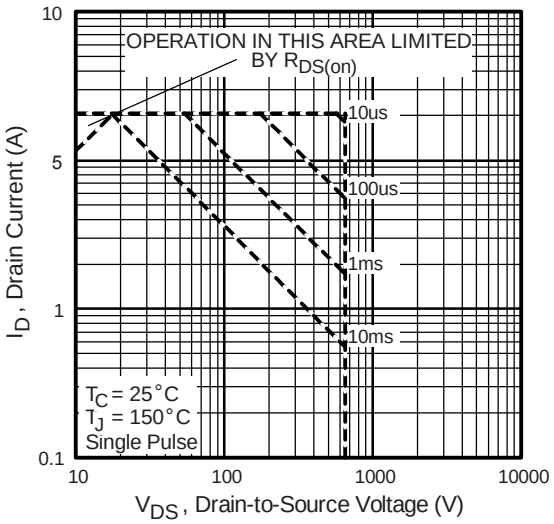


Fig. 8 - Maximum Safe Operating Area

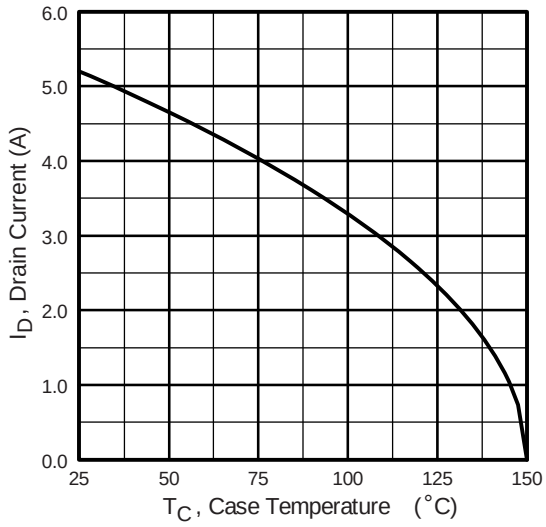


Fig. 9 - Maximum Drain Current vs. Case Temperature

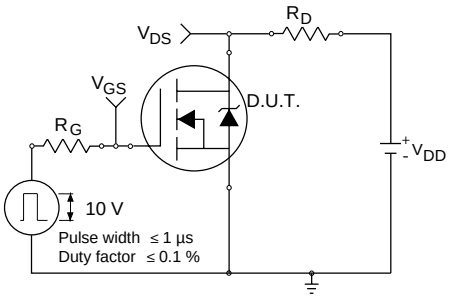


Fig. 10a - Switching Time Test Circuit

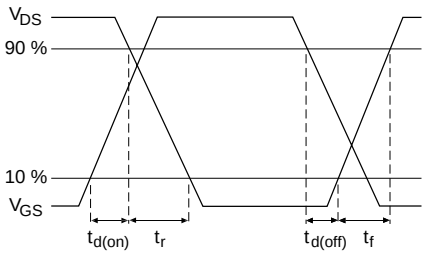


Fig. 10b - Switching Time Waveforms

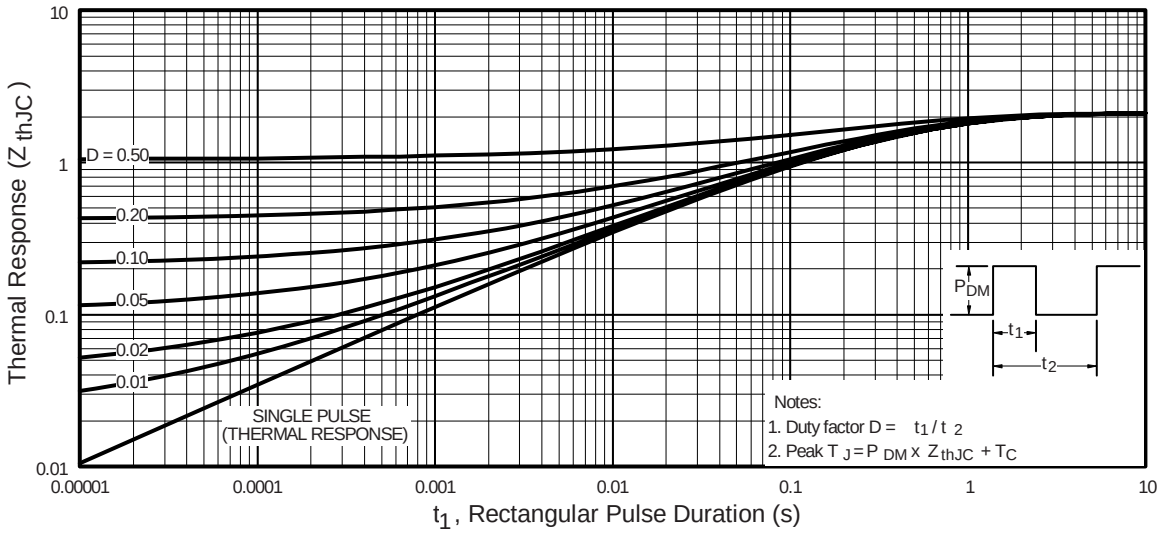


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

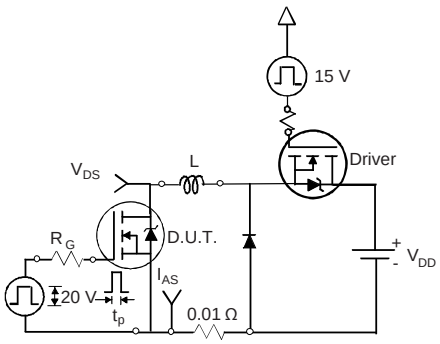


Fig. 12a - Unclamped Inductive Test Circuit

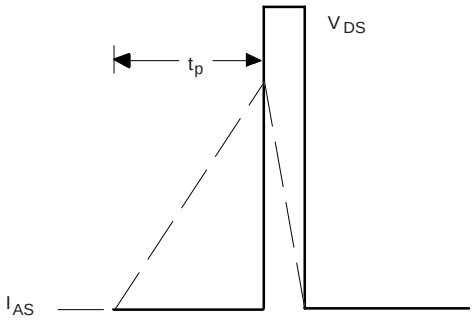


Fig. 12b - Unclamped Inductive Waveforms

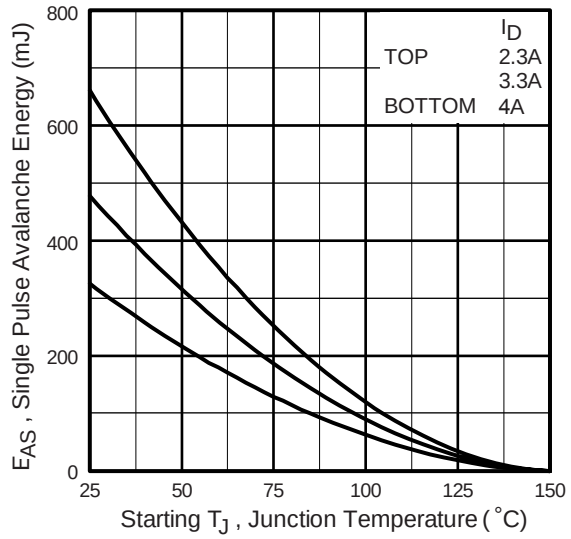


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

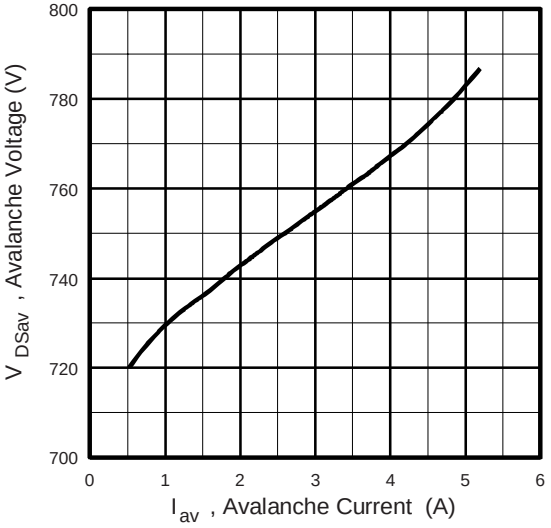


Fig. 12d - Typical Drain-to Source Voltage vs. Avalanche Current

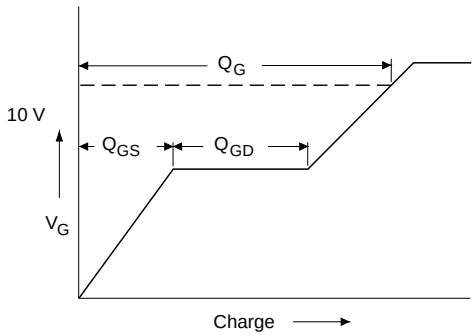


Fig. 13a - Basic Gate Charge Waveform

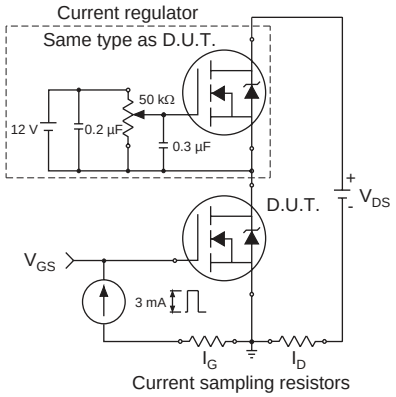
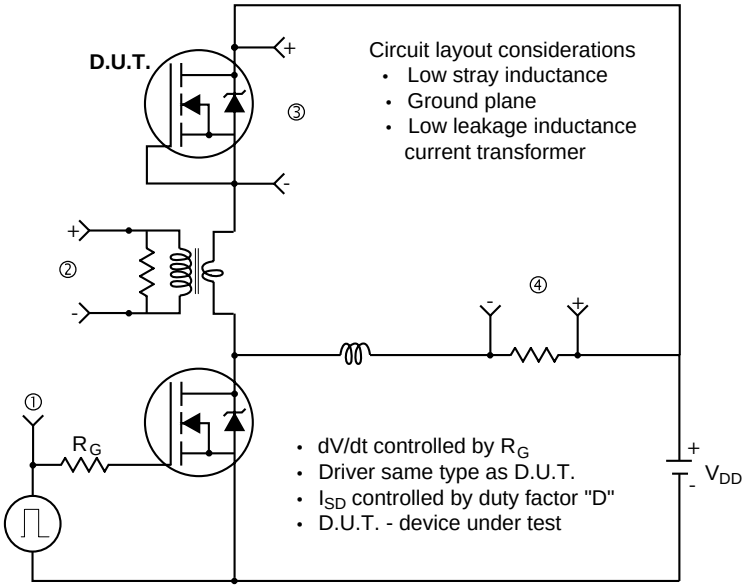
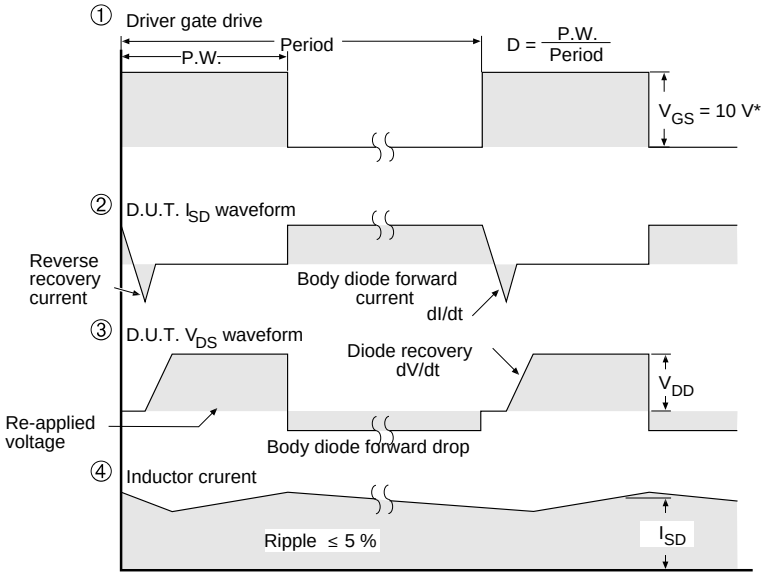


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

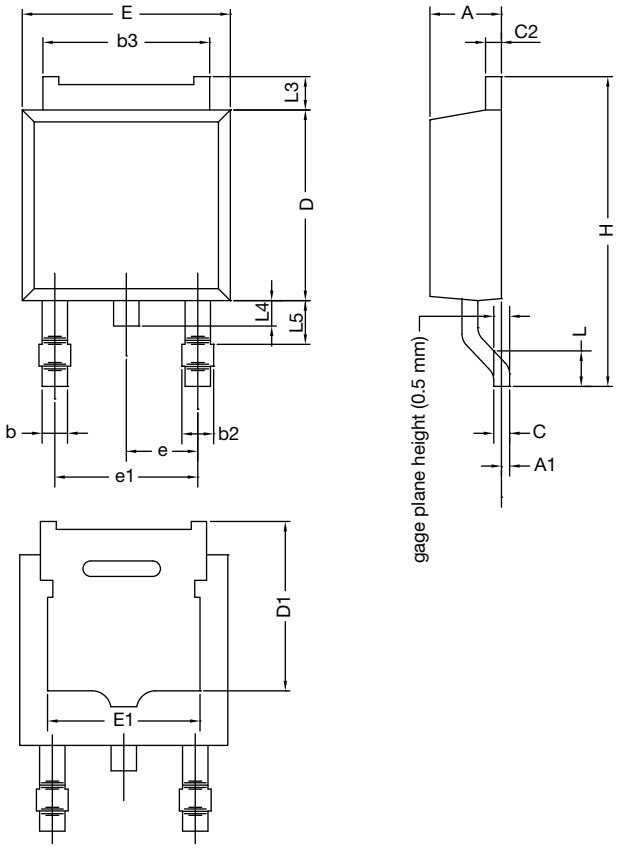




* V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

TO-252AA CASE OUTLINE



	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

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